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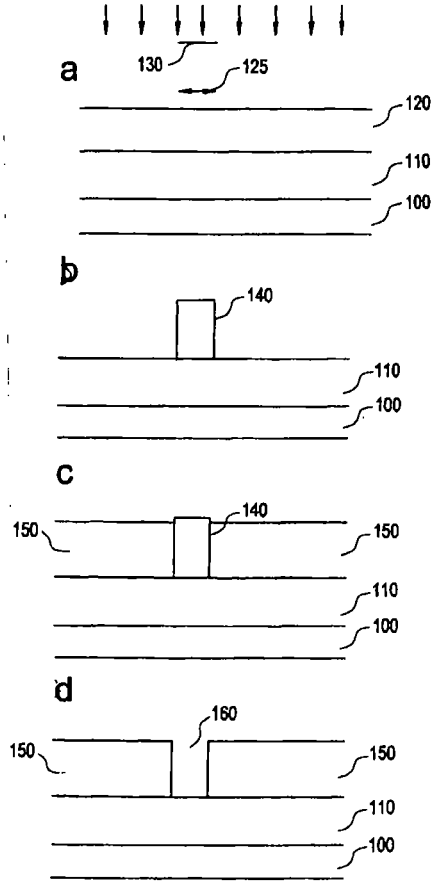
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(54) Title: BRIGHT FIELD IMAGE REVERSAL FOR CONTACT HOLE PATTERNING



(57) Abstract: A method of forming a small contact hole (160) uses a bright field mask (130) to form a small cylinder (140) in a positive resist layer (120) after exposure and developing. A negative resist layer (150) is formed around the small cylinder, and then etched or polished back to leave a top portion of the small cylinder exposed above the negative resist layer. The negative resist layer and the small cylinder (positive resist) are flood exposed to light, and then subject to a developer. What remains is a small contact hole (160) located where the small cylinder was previously located.

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ACTION

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